

Silicon PNP Power Transistors

2SB628

DESCRIPTION

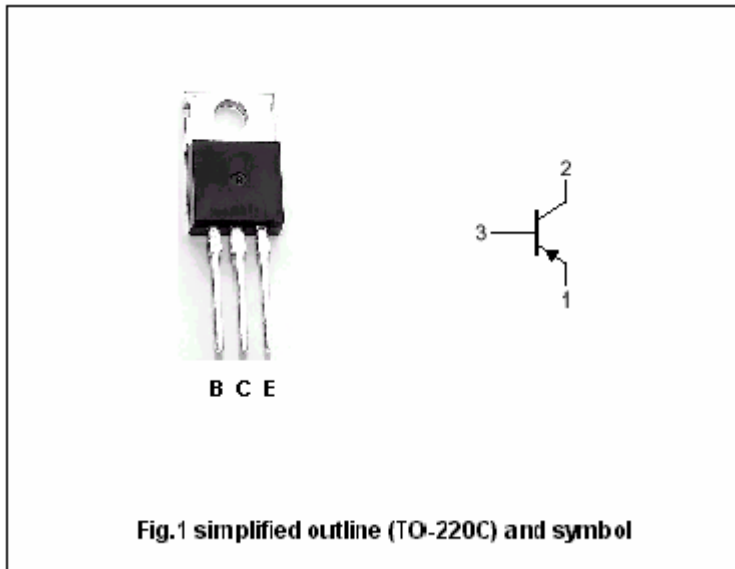
- With TO-220C package
- High V_{CEO}

APPLICATIONS

- Low frequency power amplifier color TV vertical deflection output

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



Absolute maximum ratings($T_a=25^\circ$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-160	V
V_{CEO}	Collector-emitter voltage	Open base	-160	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current		-1.5	A
P_C	Collector power dissipation	$T_C=25^\circ$	20	W
T_j	Junction temperature		150	$^\circ$
T_{stg}	Storage temperature		-45~150	$^\circ$

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-10mA; I _B =0	-160			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =-0.1mA; I _E =0	-160			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =-0.1mA; I _C =0	-5			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-0.3A; I _B =-30mA			-1.0	V
V _{BE}	Base-emitter voltage	I _C =-0.3A; V _{CE} =-4V			-1.0	V
I _{CBO}	Collector cut-off current	V _{CB} =-120V; I _E =0			-1	μA
I _{EBO}	Emitter cut-off current	V _{EB} =-4V; I _C =0			-1	μA
h _{FE}	DC current gain	I _C =-0.3A; V _{CE} =-5V	40		200	
f _T	Transition frequency	I _C =-0.3A; V _{CE} =-5V		40		MHz

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PACKAGE OUTLINE

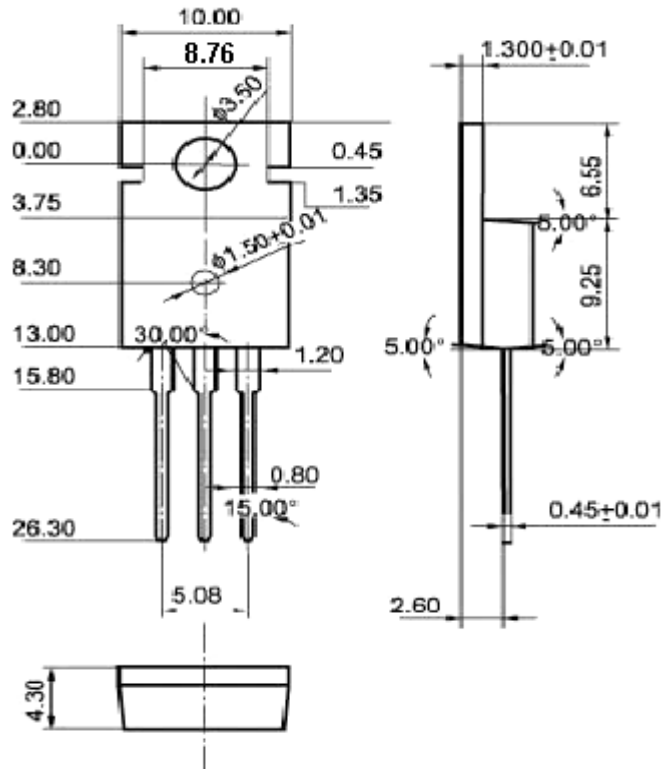


Fig.2 Outline dimensions (unindicated tolerance: ± 0.10 mm)